

TPS631012 および TPS631013 ウェハー チップ スケール パッケージに I²C 搭 載、1.6V ~ 5.5V 入力電圧 1.5A 昇降圧コンバータ

1 特長

- 入力電圧範囲:1.6V~5.5V
 - スタートアップ時のデバイス入力電圧 > 1.65V
- 出力電圧範囲 (調整可能):1.0V~5.5V
- 高い出力電流能力、3A ピーク スイッチ電流
 - V_{IN} ≧ 3V、V_{OUT} = 3.3V 時の I_{OUT} は 2A
 - V_{IN} ≧ 2.7V、V_{OUT} = 3.3V 時の I_{OUT} は 1.5A
- 全負荷範囲にわたって高効率を実現
 - 静止電流:8µA (代表値)
 - 自動パワー セーブ モードおよび強制 PWM モー ドを構成可能
- ピーク電流昇降圧モードアーキテクチャ
 - シームレスなモード遷移
 - 順方向および逆方向電流動作
 - あらかじめ出力にバイアスを印加した状態で起動
 - 2MHz スイッチングの固定周波数動作
- 安全性と堅牢な動作機能
 - 過電流保護および短絡保護
 - アクティブ ランプを採用したソフト スタート機能内
 - 過熱保護および過電圧保護
 - 負荷切断による真のシャットダウン機能
 - 順方向および逆方向の電流制限
- 内部 EN のデフォルト設定
 - TPS631012 および TPS631012X(X=1,2,3): CONVERTER EN = 0
 - TPS631013:CONVERTER EN = 1
- 小型ソリューション サイズ
 - 小型 1µH インダクタ
 - 1.803mm × 0.905mm (WCSP)

SCL SDA ΕN GND

代表的なアプリケーション

2 アプリケーション

- **TWS**
- システム・プリレギュレータ (スマートフォン、タブレット、 端末、テレマティクス)
- ポイント・オブ・ロード・レギュレーション (有線センサ、 ポート/ケーブル・アダプタ、ドングル)
- 指紋、カメラ・センサ (電子スマート・ロック、IP ネットワ ーク・カメラ)
- 電圧スタビライザ (データコム、光モジュール、冷却 / 加熱)

3 概要

TPS631012 および TPS631013 は、超小型ウェハー チ ップ スケール パッケージに封止された定周波数ピーク電 流モード制御昇降圧コンバータです。 3A のピーク電流制 限 (標準値) と 1.6V ~ 5.5V の入力電圧範囲を備え、シ ステム プリレギュレータと電圧スタビライザの電源ソリュー ションを提供します。

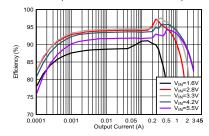
入力電圧に応じて自動的に昇圧モード、降圧モード、3サ イクル昇降圧モード (入力電圧が出力電圧とほぼ等しい 場合)で動作します。モード間の遷移は定義されたデュー ティサイクルで発生し、モード間の不要な切り替えが避け られるので出力電圧リップルを減らすことができます。8µA の静止電流とパワー セーブ モードにより、軽負荷から無 負荷までの状況で非常に高い効率を実現します。

これらのデバイスは、WCSP で非常に小型のソリューショ ンサイズを実現しています。

パッケージ情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
TPS631012	WCSP	1.803mm × 0.905mm
TPS631013 (2)	WOOF	1.000111111 4 0.900111111

- 利用可能なすべてのパッケージについては、データシートの末尾 にある注文情報を参照してください。
- 開発中製品情報 (量産データではありません)。



効率と出力電流との関係 (V_{OUT} = 3.3V)



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4 Device Comparison Table

PART NUMBER	Default Setting of Internal EN ⁽³⁾	I ² C Target Address
TPS631012	CONVERTER_EN = 0	0x2A
TPS6310121 ⁽¹⁾ ⁽²⁾	CONVERTER_EN = 0	0x28
TPS6310122 ⁽¹⁾ (2)	CONVERTER_EN = 0	0x29
TPS6310123 ⁽¹⁾ ⁽²⁾	CONVERTER_EN = 0	0x2B
TPS631013 ⁽¹⁾ (2)	CONVERTER_EN = 1	0x2A

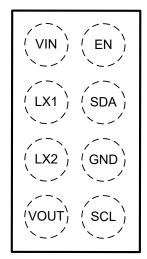
- (1)
- Product Preview. Contact TI factory for more information. TPS631012 and TPS631012X(X = 1, 2, 3) differ only in the I2C target address. Refer to the Register CONTROL1.
- (2)

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Product Folder Links: TPS631012 TPS631013

5 Pin Configuration and Functions



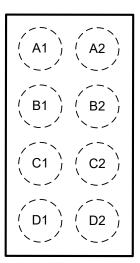


図 5-1. 8-Pin YBG WCSP Package (Top View)

表 5-1. Pin Functions

P	IN	I/O ⁽¹⁾	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
VIN	A1	PWR	Supply input voltage	
EN	A2	I	Device enable. Set high to enable and low to disable. It must not be left floating.	
LX1	B1	PWR	Inductor switching node of the buck stage	
SDA	B2	I	I ² C serial interface data. Pull this pin up to the I ² C bus voltage with a resistor.	
LX2	C1	PWR	Inductor switching node of the boost stage	
GND	C2	PWR	Power ground	
VOUT	D1	PWR	Power stage output	
SCL	D2	I	I ² C serial interface clock. Pull this pin up to the I ² C bus voltage with a resistor.	

(1) PWR = power, I = input



6 Specifications

6.1 Absolute Maximum Ratings

over operating junction temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Vı	Input voltage (VIN, LX1, LX2, VOUT, EN, SCL, SDA) ⁽²⁾	-0.3	6.0	V
"	Input voltage for less than 10 ns (LX1, LX2) ⁽²⁾	-2.0	7.0	V
T_J	Operating junction temperature	-40	150	°C
T _{stg}	Storage temperature	-65	150	°C

⁽¹⁾ Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Rating

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±1000	V
V _(ESD)	Liectiostatic discharge	Charged-device model (CDM), per JEDEC specification JS-002 ⁽²⁾	± 500	

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature (unless otherwise noted)

			MIN	NOM	MAX	UNIT
VI	Supply voltage		1.6		5.5	V
Vo	Output voltage		1.0		5.5	V
Cı	Effective Input capacitance	V _I = 1.6 V to 5.5 V	4.2			μF
Co		$1.2 \text{ V} \le \text{V}_{\text{O}} \le 3.6 \text{ V}$, nominal value at $\text{V}_{\text{O}} = 3.3 \text{ V}$	10.4	16.9	330	μF
0	Effective Output capacitance	$3.6 \text{ V} < \text{V}_{\text{O}} \le 5.5 \text{ V}$, nominal value at $\text{V}_{\text{O}} = 5 \text{ V}$	7.95	10.6	330	μF
L	Effective Inductance		0.7	1	1.3	μH
T _J	Operating junction temperature range		-40		125	°C

6.4 Thermal Information

over operating free-air temperature range (unless otherwise noted)

		TPS631012 TPS631013	
THERMAL METRIC		YBG(WCSP)	UNIT
		8 pins	
R _{⊙JA}	Junction-to-ambient thermal resistance	84	°C/W
R _{OJC(top)}	Junction-to-case (top) thermal resistance	0.7	°C/W
R _{⊝JB}	Junction-to-board thermal resistance	43.9	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	2.9	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	43.7	°C/W
$R_{\Theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

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⁽²⁾ All voltage values are with respect to network ground terminal, unless otherwise noted.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.5 Electrical Characteristics

Over operating junction temperature range and recommended supply voltage range (unless otherwise noted). Typical values are at $V_1 = 3.8 \text{ V}$, $V_0 = 3.3 \text{ V}$ and $T_1 = 25 ^{\circ}\text{C}$ (unless otherwise noted).

	PARAMETER		TEST C	ONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY								
I _{SD}	Shutdown current into VIN		V _I = 3.8 V, V _(EN) = 0 V	T _J = 25°C		0.5	0.9	μA
IQ	Quiescent current into VIN		V _I = 2.2 V, V _O = 3.3 V, V _{(EN}) = 2.2 V, no switching		0.15	6.1	μA
IQ	Quiescent current into VOUT	-	V _I = 2.2 V, V _O = 3.3 V, V _{(EN}) = 2.2 V, no switching		8		μA
V _{IT+}	Positive-going UVLO thresho	old voltage	V _I rising	,	1.5	1.55	1.599	V
V _{IT-}	Negative-going UVLO thresh	old voltage	V _I falling		1.4	1.45	1.499	V
V _{hys}	UVLO threshold voltage hyst	eresis			99			mV
V _{I(POR)T+}	Positive-going POR threshol	d voltage ⁽¹⁾	maximum of V _I or V _O		1.25	1.45	1.65	V
V _{I(POR)T-}	Negative-going POR thresho	old voltage ⁽¹⁾			1.22	1.43	1.6	V
I/O SIGNAL								
V _{T+}	Positive-going threshold voltage	EN, SDA, SCL			0.77	0.98	1.2	V
V _{T-}	Negative-going threshold voltage	EN, SDA, SCL			0.5	0.66	0.76	V
V _{hys}	Hysteresis voltage	EN, SDA, SCL				300		mV
I _{IH}	High-level input current	EN, SDA, SCL	$V_{(EN)} = V_{(SDA)} = V_{(SCL)} = 1.5$ no pullup resistor	5 V,		±0.01	±0.25	μA
I _{IL}	Low-level input current	EN, SDA, SCL	$V_{(EN)} = V_{(SDA)} = V_{(SCL)} = 0 \text{ V},$			±0.01	±0.1	μA
I _{IB}	Input bias current	EN, SDA, SCL	V _(EN) = 5.5 V			±0.01	±0.3	μA
POWER SV	WITCH							
		Q1				45		mΩ
	On-state resistance	Q2	$V_1 = 3.8 \text{ V}, V_0 = 3.3 \text{ V},$			50		mΩ
r _{DS(on)}	On-State resistance	Q3	test current = 0.2 A			50		mΩ
		Q4				85		mΩ
CURRENT	LIMIT							
				Output sourcing current	2.6	3	3.35	Α
I _{L(PEAK)}	Switch peak current limit (2)	Q1	V _O = 3.3 V	Output sinking current, V _I = 3.3 V	-0.7	-0.55	-0.45	Α
I _{PFM_entry}	PFM mode entry threshold (p	oeak) current	I _O falling			145		mA
PROTECTI	ION FEATURES							
V _{T+(OVP)}	Positive-going OVP threshold voltage	d			5.55	5.75	5.95	V
V _{T+(IVP)}	Positive-going IVP threshold voltage				5.55	5.75	5.95	V
T _{SD_R}	Thermal shutdown threshold	temperature	T _J rising			160		°C
T _{SD_HYS}	Thermal shutdown hysteresis	S				25		°C
TIMING PA	RAMETERS							
	Delay between a rising edge					0.87	1.5	ms
$t_{d(EN)}$	and the start of the output vo	itage ramp					I	
t _{d(ramp)}	Soft-start ramp time	itage ramp			6.42	7.55	8.68	ms

⁽¹⁾ The POR (Power On Reset) threshold is the minimum supply of the internal VMAX block that allows the device to operate

⁽²⁾ Current limit production test are performed under DC conditions. The current limit in operation is somewhat higher and depending on propagation delay and the applied external components



6.6 Timing Requirements

Over operating junction temperature range and recommended supply voltage range (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN NOM	MAX	UNIT
I ² C INTERFA	CE				
		Standard mode	0	100	
f _{SCL}	SCL clock frequency	Fast mode	0	400	kHz
		Fast mode plus ⁽¹⁾	0	1000	
		Standard mode	4.7		
t _{LOW}	LOW period of the SCL clock	Fast mode	1.3		μs
		Fast mode plus ⁽¹⁾	0.5		
		Standard mode	4.0		
HIGH period of the SCL clock	Fast mode	0.6		μs	
		Fast mode plus ⁽¹⁾	0.26		
		Standard mode	4.7		
t _{BUF}	Bus free time between a STOP and a START condition	Fast mode	1.3		μs
		Fast mode plus ⁽¹⁾	0.5		
		Standard mode	4.7		
tsu:sta	Set-up time for a repeated START condition	Fast mode	0.6		μs
	Condition	Fast mode plus ⁽¹⁾	0.26		
		Standard mode	4.0		
HD:STA	D:STA Hold time (repeated) START condition	Fast mode	0.6		μs
		Fast mode plus ⁽¹⁾	0.26		
		Standard mode	0		
t _{HD:DAT}	Data hold time	Fast mode	0		μs
		Fast mode plus ⁽¹⁾	0		
		Standard mode		1000	
t _r	Rise time of both SDA and SCL signals	Fast mode	20	300	ns
	Signals	Fast mode plus ⁽¹⁾		20	
		Standard mode		300	
	Fall time of both SDA and SCL	Fast mode	20×V _{DD} /	300	
t _f	signals	- dot mede	5.5		ns
		Fast mode plus ⁽¹⁾	20×V _{DD} / 5.5	120	
		Standard mode	4.0		
su:STO	Set-up time for STOP condition	Fast mode	0.6		μs
		Fast mode plus ⁽¹⁾	0.26		
		Standard mode		3.45	
VD;DAT	Data valid time	Fast mode		0.9	μs
		Fast mode plus (1)		0.45	
		Standard mode		3.45	
VD;ACK	Data valid acknowledge time	Fast mode		0.9	μs
•		Fast mode plus ⁽¹⁾		0.45	
•		Standard mode		400	
C _b	Capacitive load for each bus line	Fast mode		400	pF

⁽¹⁾ Fast mode plus is compatible but not compliant with I^2C standard

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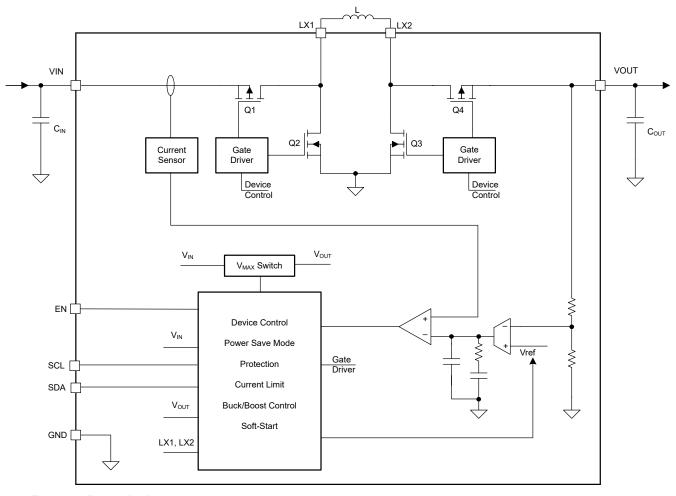
Product Folder Links: TPS631012 TPS631013

7 Detailed Description

7.1 Overview

The TPS631012 and TPS631013 are constant frequency peak current mode control buck-boost converters. The converters use a fixed-frequency with approximately 2-MHz switching frequency. The modulation scheme has three clearly defined operation modes where the converters enter with defined thresholds over the full operation range of V_{IN} and V_{OUT} . The maximum output current is determined by the Q1 peak current limit, which is typically 3 A.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Undervoltage Lockout (UVLO)

The input voltage of the VIN pin is continuously monitored if the device is not in shutdown mode. UVLO only stops or starts the converter operation. The UVLO does not impact the core logic of the device. UVLO avoids a brownout of the device during device operation. In case the supply voltage on the VIN pin is lower than the negative-going threshold of UVLO, the converter stops its operation. To avoid a false disturbance of the power conversion, the UVLO falling threshold logic signal is digitally de-glitched.

If the supply voltage on the VIN pin recovers to be higher than the UVLO rising threshold, the converter returns to operation. In this case, the soft-start procedure restarts faster than under start-up without a pre-biased output.



7.3.2 Enable and Soft Start

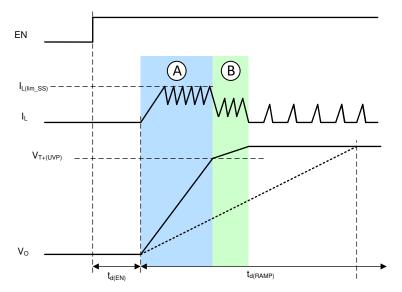


図 7-1. Typical Soft-Start Behavior

When the input voltage is above the UVLO rising threshold and the EN pin is pulled to a voltage above 1.2 V, the TPS631012 and TPS631013 are enabled and start up after a short delay time, $t_{d(EN)}$.

The TPS631012 and TPS631013 have two start-up mechanisms that are controlled by the FAST_RAMP_EN bit in Register CONTROL2. ☒ 7-1 shows a typical start-up case (low output load, typical output capacitance).

- When FAST_RAMP_EN = 1, the fast ramp mode is enabled. The output ramp behavior is shown as the solid line Vo in ⋈ 7-1
- When FAST_RAMP_EN = 0, the fast ramp mode is disabled. The output ramp behavior is shown as the dash line Vo in ⋈ 7-1

When fast ramp mode is enabled, the devices control the inductor peak current to limit the inrush current and ensure the fastest possible soft start if the capacitance is chosen lower than that for which the ramp time $t_{d(RAMP)}$ was selected. The output voltage then rises faster than the reference voltage ramp (see phase A in \boxtimes 7-1). To avoid an output overshoot, the current clamp is deactivated when the output is close to the target voltage and follows the reference voltage ramp slew value given by the voltage ramp, which is finishing the start up (see phase B in \boxtimes 7-1). Transition from the current clamp operation is detected using the $V_{T+(UVP)}$ threshold, which is typically 90% of the target output voltage. After phase B, the output voltage is well regulated to the nominal target voltage. The current waveform depends on the output load and operation mode. The current limit during start-up has two options and is controlled by the CL_RAMP_MIN bit in Register CONTROL2.

- When CL_RAMP_MIN = 0, the typical current limit during start-up (phase A in ☒ 7-1) is 500mA

When fast ramp mode is disabled, the output voltage is totally controlled by the internal reference voltage ramp slew rate. There are three bits of TD_RAMP in Register CONTROL2 to define the output voltage ramp time.

Note that if, during start-up, the current limit $(I_{L(lim_SS)})$ is lower than the current required to follow the voltage ramp controlled by TD_RAMP, the current automatically increases to follow the voltage ramp.

7.3.3 Device Enable (EN)

The EN pin enables and disables the device.

- When the EN pin is high, the device is enabled.
- When the EN pin is low, the device is disabled.

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The CONVERTER_EN bit in the Register CONTROL1 can also be used to enable and disable the output of the converter.

- For TPS631012, the default bit of CONVERTER_EN = 0.
- For TPS631013, the default bit of CONVERTER_EN = 1.

表 7-1. Device Enable Truth Table

EXTERNAL EN PIN	INTERNAL EN (CONVERTER_EN)	DEVICE STATE	OUTPUT STATE
0	X	Device in Shutdown	No Output
1	0	Programming Interface Active	No Output
1	1	Device Active	Output Enabled

Note that when the EN pin is connected to logic low, all the I²C registers are cleaned and reset to the default values. While setting CONVERTER_EN to 0 has no influences on the I²C registers

7.3.4 Output Voltage Control

The TPS631012 and TPS631013 can generate output voltages from 1.0 V to 5.5 V with a 25 mV step. The Register VOUT is used to set the output voltage:

- VOUT = $1.000 + (VOUT[7:0] \times 0.025) \text{ V}$, when $0x00 \le VOUT[7:0] \le 0xB4$;
- VOUT = 5.5 V, when 0xB5<=VOUT[7:0]<=0xFF

VOUT[7:0] is the 8-bit value in the Register VOUT.

The dynamic voltage scaling control bit of EN_FAST_DVS in Register CONTROL1 controls the VOUT settling time when VOUT is set between different voltages.

- When EN FAST DVS = 1, the typical VOUT slew rate is 7.2 V/ms;
- When EN FAST DVS = 0, the typical VOUT slew rate is 0.4 V/ms

7.3.5 Mode Selection (PFM/FPWM)

The TPS631012 and TPS631013 have two modes of PFM and FPWM. During PFM mode operation, the devices feature a power save mode to maintain the highest efficiency over the full operating output current range. In PFM mode the devices automatically change the converter operation from CCM to pulse frequency modulation. During FPWM mode, the devices use PWM for all operating conditions regardless of the output current to achieve minimum output ripple.

The PFM/FPWM mode selection is controlled by the FPWM bit in Register CONTROL2:

- When FPWM = 0b0, the devices work in PFM mode
- When FPWM = 0b1, the devices work in FPWM mode

7.3.6 Output Discharge

The TPS631012 and TPS631013 provide an active pull down current to quickly discharge output when the EN pin is logic low or the CONVERTER_EN bit is set to 0. With this function, the VOUT is connected to ground through internal circuitry, preventing the output from "floating" or entering into an undetermined state. The output discharge function makes the power on and off sequencing smooth. Pay attention to the output discharge function if use this device in applications such as power multiplexing, because the output discharge circuitry creates a constant current path between the multiplexer output and the ground.

The output discharge is controlled by the two bits named with EN_DISCH_VOUT. The output discharge can be disabled or set to three different options. Please refer to the EN_DISCH_VOUT bits in Register CONTROL2 for detailed I²C settings.

7.3.7 Reverse Current Operation

The device can support reverse current operation (the current flows from VOUT pin to VIN pin) in FPWM mode. If the internal output feedback voltage is higher than the reference voltage, the converter regulation forces a

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current into the input capacitor. The reverse current operation is independent of the V_{IN} voltage or V_{OUT} voltage ratio, hence it is possible on all device operation modes boost, buck, or buck-boost.

7.3.8 Protection Features

The following sections describe the protection features of the device.

7.3.8.1 Input Overvoltage Protection

The TPS631012 and TPS631013 have input overvoltage protection which avoids any damage to the device in case the current flows from the output to the input and the input source cannot sink current (for example, a diode in the supply path).

If forced PWM mode is active, the current can go negative until it reaches the sink current limit. Once the input voltage threshold, $V_{T+(IVP)}$, is reached on the VIN pin, the protection disables forced PWM mode and only allows current to flow from VIN to VOUT. After the input voltage drops under the input voltage protection threshold, forced PWM mode can be activated again.

7.3.8.2 Output Overvoltage Protection

The devices have the output overvoltage protection which avoids any damage to the device. When the output voltage threshold $V_{T+(OVP)}$ is reached on the VOUT pin, the protection disables the converter power stage and makes the switching nodes high impedance.

7.3.8.3 Short Circuit Protection/Hiccup

The device features peak current limit performance at short circuit protection. 🗵 7-2 shows a typical device behavior of an short/overload event of the short circuit protection.

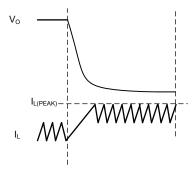


図 7-2. Typical Device Behavior During Short Circuit Protection

When the EN_SCP bit in Register CONTROL1 is set to 1 to enable the short circuit hiccup protection, the hiccup timer works, limiting the switching on time to a typical 9 ms followed by a typical off time of 22 ms, then the device restarts. If the short condition disappears, the device automatically enters the normal working mode.

7.3.8.4 Thermal Shutdown

To avoid thermal damage of the device, the temperature of the die is monitored. The device stops operation once the sensed temperature rises over the typical thermal threshold 160 °C. After the temperature drops below the typical thermal shutdown hysteresis 25 °C, the converter returns to normal operation.

7.4 Device Functional Modes

The device has two functional modes: off and on. The device enters the on mode when the voltage on the VIN pin is higher than the UVLO threshold and a high logic level is applied to the EN pin. The device enters the off mode when the voltage on the VIN pin is lower than the UVLO threshold or a low logic level is applied to the EN pin.

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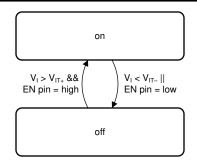


図 7-3. Device Functional Modes

7.5 Programming

7.5.1 Serial Interface Description

I²C is a 2-wire serial interface developed by Philips Semiconductor, now NXP Semiconductors (see *NXP Semiconductors, UM10204 – I²C-Bus Specification and User Manual*). The bus consists of a data line (SDA) and a clock line (SCL) with pullup structures. When the bus is idle, both SDA and SCL lines are pulled high. All the I²C-compatible devices connect to the I²C bus through open-drain I/O pins, SDA, and SCL. A controller device, usually a microcontroller or a digital signal processor, controls the bus. The controller is responsible for generating the SCL signal and device addresses. The controller also generates specific conditions that indicate the START and STOP of data transfer. A target device receives and transmits data on the bus under control of the controller device.

The device works as a target and supports the following data transfer modes, as defined in the I^2C -Bus Specification:

- Standard-mode (100 kbps)
- Fast-mode (400 kbps)
- Fast-mode Plus (1 Mbps)

The interface adds flexibility to the power supply solution, enabling most functions to be programmed to new values, depending on the instantaneous application requirements. Register contents remain intact as long as supply voltage remains above $V_{\text{IT+(POR)}}$.

The data transfer protocol for standard and fast modes is exactly the same, therefore, it is referred to as F/S-mode in this document. The device supports 7-bit addressing; 10-bit addressing and general call address are not supported. The device 7-bit address is 2Ah (00101010b).

To make sure that the I^2C function in the device is correctly reset, it is recommended that the I^2C controller initiates a STOP condition on the I^2C bus after the initial power up of SDA and SCL pullup voltages.

7.5.2 Standard-, Fast-, and Fast-Mode Plus Protocol

The controller initiates a data transfer by generating a start condition. The start condition is when a high-to-low transition occurs on the SDA line while SCL is high, as shown in \boxtimes 7-4. All I²C-compatible devices recognize a start condition.

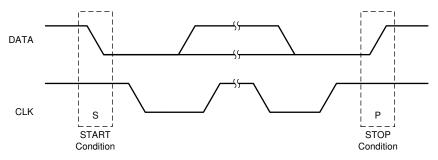


図 7-4. START and STOP Conditions

Product Folder Links: TPS631012 TPS631013

The controller then generates the SCL pulses and transmits the 7-bit address and the read/write direction bit, R/W, on the SDA line. During all transmissions, the controller ensures that data is valid. A valid data condition requires the SDA line to be stable during the entire high period of the clock pulse (see \boxtimes 7-5). All devices recognize the address sent by the controller and compare it to their internal fixed addresses. Only the target device with a matching address generates an acknowledge (see \boxtimes 7-6) by pulling the SDA line low during the entire high period of the ninth SCL cycle. Upon detecting this acknowledge, the controller knows that communication link with a target has been established.

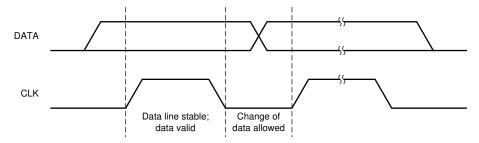
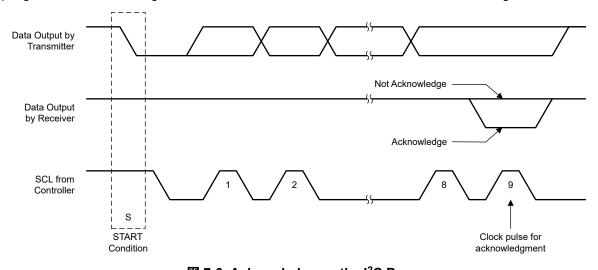


図 7-5. Bit Transfer on the Serial Interface

The controller generates further SCL cycles to either transmit data to the target (R/W bit 1) or receive data from the target (R/W bit 0). In either case, the receiver needs to acknowledge the data sent by the transmitter. An acknowledge signal can either be generated by the controller or by the target, depending on which one is the receiver. 9-bit valid data sequences consisting of 8-bit data and 1-bit acknowledge can continue as long as necessary.

To signal the end of the data transfer, the controller generates a stop condition by pulling the SDA line from low to high while the SCL line is high (see \boxtimes 7-4). This low level to high level transition on the SDA line when the SCL is at high releases the bus and stops the communication link with the addressed target. All I^2 C-compatible devices must recognize the stop condition. Upon the receipt of a stop condition, all devices know that the bus is released and they wait for a start condition followed by a matching address.

Attempting to read data from register addresses not listed in this section results in 00h being read out.



☑ 7-6. Acknowledge on the I²C Bus



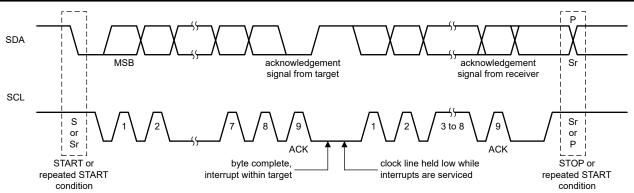


図 7-7. Bus Protocol

7.5.3 I²C Update Sequence

A single update requires the following:

- · A start condition
- A valid I²C target address
- · A register address
- · A data byte

To acknowledge the receipt of each byte, the device pulls the SDA line low during the high period of a single clock pulse. The device performs an update on the falling edge of the acknowledge signal that follows the last byte.

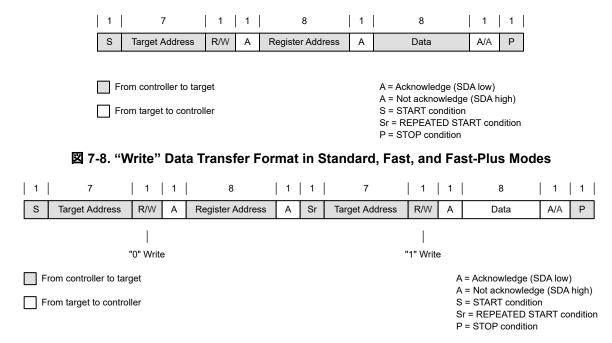


図 7-9. "Read" Data Transfer Format in Standard, Fast, and Fast-Plus Modes

7.6 Register Map

7.6.1 Register Description

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7.6.1.1 Register Map

表 7-2. Register Map

ADDRESS	ACRONYM	REGISTER NAME	SECTION
0x02	CONTROL1	Control 1 Register	Go
0x03	VOUT	VOUT Register	Go
0x05	CONTROL2	Control 2 Register	Go

7.6.1.2 Register CONTROL1 (Register address: 0x02; Default: 0x08)

Return to Register Map

表 7-3. Register CONTROL1 Format

7	6	5 4		3	2	1	0
	NIL	[3:0]		EN_FAST_DVS	EN_SCP	NIL	CONVERTER_EN
R				R/W	R/W	R	R/W

LEGEND: R/W = Read/Write; R = Read only

SCP: Short Circuit Protection

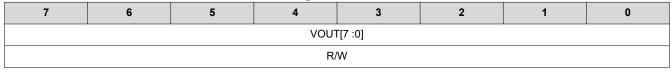
表 7-4. Register CONTROL1 Field Descriptions

Bit	Field	Туре	Reset	Description
7:4	NIL[3:0]	R	0b0000	Not used. During write operations data for these bits are ignored. During read operations 0 is returned
3	EN_FAST_DVS	R/W	0b1	Sets DVS to fast mode 0 : DISABLE, 1 : ENABLE
2	EN_SCP	R/W	0b0	Enable short circuit hiccup protection 0 : DISABLE, 1 : ENABLE
1	NIL	R	0b0	Not used.
0	CONVERTER_EN	R/W	0b0	Enable Converter ('AND'ed with EN-pin) 0 : DISABLE, 1 : ENABLE

7.6.1.3 Register VOUT (Register address: 0x03; Default: 0x5C)

Return to Register Map

表 7-5. Register VOUT Format



LEGEND: R/W = Read/Write

表 7-6. Register VOUT Field Descriptions

Bit	Field	Туре	Reset	Description
7:0	VOUT[7:0]	R/W	0x5C	These bits set the output voltage Output voltage = 1.000 + (VOUT[7:0] × 0.025) V when 0x00<=VOUT[7:0]<=0xB4; Output voltage = 5.5 V when 0xB5<=VOUT[7:0]<=0xFF

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7.6.1.4 Register CONTROL2 (Register address: 0x05; Default: 0x45)

Return to Register Map

表 7-7. Register CONTROL2 Format

7	6	5	4	3	2	1	0
FPWM	FAST_RAMP_EN	EN_DISCH	_VOUT[1:0]	CL_RAMP_MIN	TD_RAMP[2:0]		
R/W	R/W	R/	W	R/W		R/W	

LEGEND: R/W = Read/Write

表 7-8. Register CONTROL2 Field Descriptions

Bit	Field	Туре	Reset	Description
7	FPWM	R/W	0b0	Force PWM operation 0 : DISABLE, 1 : ENABLE
6	FAST_RAMP_EN	R/W	0b1	Device can start-up faster than VOUT ramp 0 : DISABLE, 1 : ENABLE
5:4	EN_DISCH_VOUT[1:0]	R/W	0600	Enable of BUBO Vout Discharge 00 : DISABLE 01 : SLOW (34mA) 10 : MEDIUM (67mA) 11 : FAST (100mA)
3	CL_RAMP_MIN	R/W	0b0	Define the minimum current limit during the soft start ramp 0 : Low (500mA) 1 : High (2x Low)
2:0	TD_RAMP[2:0]	R/W	0b101	Defines the ramp time for the Vo soft start ramp 000: 0.256ms 001: 0.512ms 010: 1.024ms 011: 1.920ms 100: 3.584ms 101: 7.552ms 110: 9.600ms 111: 24.320ms

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8 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TPS631012 and TPS631013 are high-efficiency, low-quiescent current, buck-boost converters. The devices are suitable for applications needing a regulated output voltage from an input supply that can be higher or lower than the output voltage.

8.2 Typical Application

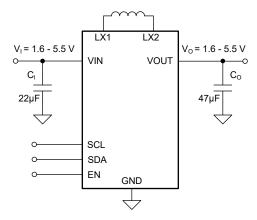


図 8-1. 3.3-V_{OUT} Typical Application

8.2.1 Design Requirements

The design parameters are listed in 表 8-1.

表 8-1. Design Parameters

PARAMETERS	VALUES
Input voltage	2.7 V to 4.3 V
Output voltage	3.3 V
Output current	1.5 A

8.2.2 Detailed Design Procedure

The first step is the selection of the output filter components. To simplify this process, $\forall \cancel{D} \cancel{>} \exists \cancel{>} 5.3$ outlines minimum and maximum values for inductance and capacitance. Pay attention to the tolerance and derating when selecting nominal inductance and capacitance.

8.2.2.1 Inductor Selection

The inductor selection is affected by several parameters such as the following:

- Inductor ripple current
- Output voltage ripple
- · Transition point into power save mode
- Efficiency

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See 表 8-2 for typical inductors.

For high efficiencies, the inductor with a low DC resistance is needed to minimize conduction losses. Especially at high-switching frequencies, the core material has a high impact on efficiency. When using small chip inductors, the efficiency is reduced mainly due to higher inductor core losses. Core losses need to be considered when selecting the appropriate inductor. The inductor value determines the inductor ripple current. The larger the inductor value, the smaller the inductor ripple current and the lower the conduction losses of the converter. Conversely, larger inductor values cause a slower load transient response. To avoid saturation of the inductor, the peak current for the inductor in steady state operation is calculated using \pm 2. Only the equation that defines the switch current in boost mode is shown because this provides the highest value of current and represents the critical current value for selecting the right inductor.

Duty Cycle Boost
$$D = \frac{V_{OUT} - V_{IN}}{V_{OUT}}$$
 (1)

$$I_{PEAK} = \frac{Iout}{\eta \times (1 - D)} + \frac{Vin \times D}{2 \times f \times L}$$
(2)

where:

- D = duty cycle in boost mode
- *f* = converter switching frequency (typical 2 MHz)
- L = inductor value
- η = estimated converter efficiency (use the number from the efficiency curves or 0.9 as an assumption)

注

The calculation must be done for the minimum input voltage in boost mode.

Calculating the maximum inductor current using the actual operating conditions gives the minimum saturation current of the inductor needed. It is recommended to choose an inductor with a saturation current 20% higher than the value calculated using \pm 2. Possible inductors are listed in \pm 8-2.

表 8-2. List of Recommended Inductors

INDUCTOR VALUE [µH]	SATURATION CURRENT [A]	DCR [mΩ]	PART NUMBER	MANUFACTURER ⁽¹⁾	SIZE (L × W × H mm)
1	4.3	42	DFE252012P-1R0M=P2	MuRata	2.5 × 2.0 × 1.2
1	4.2	43	HTEK20161T-1R0MSR	Cyntec	2.0 × 1.6 × 1.0
1	2.2	75	MAKK2016T1R0M (2)	Taiyo Yuden	2.0 × 1.6 × 1.0
1	2.0	144	DFE18SAN1R0ME0 (2)	Murata	1.6 × 0.8 × 0.8

- (1) See the セクション 9.1.1.
- (2) This inductor does not support full output current range.

8.2.2.2 Output Capacitor Selection

For the output capacitor, use small ceramic capacitors placed as close as possible to the VOUT and PGND pins of the IC. The recommended total nominal output capacitor value is 47 μ F. If, for any reason, the application requires the use of large capacitors that cannot be placed close to the IC, use a smaller ceramic capacitor in parallel to the large capacitor, and place the small capacitor as close as possible to the VOUT and PGND pins of the IC.

It is important that the effective capacitance is given according to the recommended value in 2000×6.3 . In general, consider DC bias effects resulting in less effective capacitance. The choice of the output capacitance is mainly a tradeoff between size and transient behavior as higher capacitance reduces transient response over/ undershoot and increases transient response time. Possible output capacitors are listed in $\frac{1}{5}$ 8-3.

表 8-3. List of Recommended Capacitors

CAPACITOR VALUE [µF]	VOLTAGE RATING [V]	ESR [mΩ]	PART NUMBER	MANUFACTURER ⁽¹⁾	SIZE (METRIC)
47	6.3	10	GRM219R60J476ME44	Murata	0805 (2012)
47	10	40	CL10A476MQ8QRN	Semco	0603 (1608)

(1) See the セクション 9.1.1.

8.2.2.3 Input Capacitor Selection

A 22- μ F input capacitor is recommended to improve line transient behavior of the regulator and EMI behavior of the total power supply circuit. An X5R or X7R ceramic capacitor placed as close as possible to the VIN and PGND pins of the IC is recommended. This capacitance can be increased without limit. If the input supply is located more than a few inches from the converter, additional bulk capacitance can be required in addition to the ceramic bypass capacitors. An electrolytic or tantalum capacitor with a value of 47 μ F is a typical choice.

表 8-4. List of Recommended Capacitors

CAPACITOR VALUE [µF]	VOLTAGE RATING [V]	ESR [mΩ]	PART NUMBER	MANUFACTURER ⁽¹⁾	SIZE (METRIC)
22	6.3	43	GRM187R61A226ME15	Murata	0603 (1608)
10	10	40	GRM188R61A106ME69	Murata	0603 (1608)

(1) See the セクション 9.1.1.

8.2.2.4 Setting the Output Voltage

The output voltage is set by I²C. Please refer to the part of Output Voltage Control for the detailed output voltage settings.

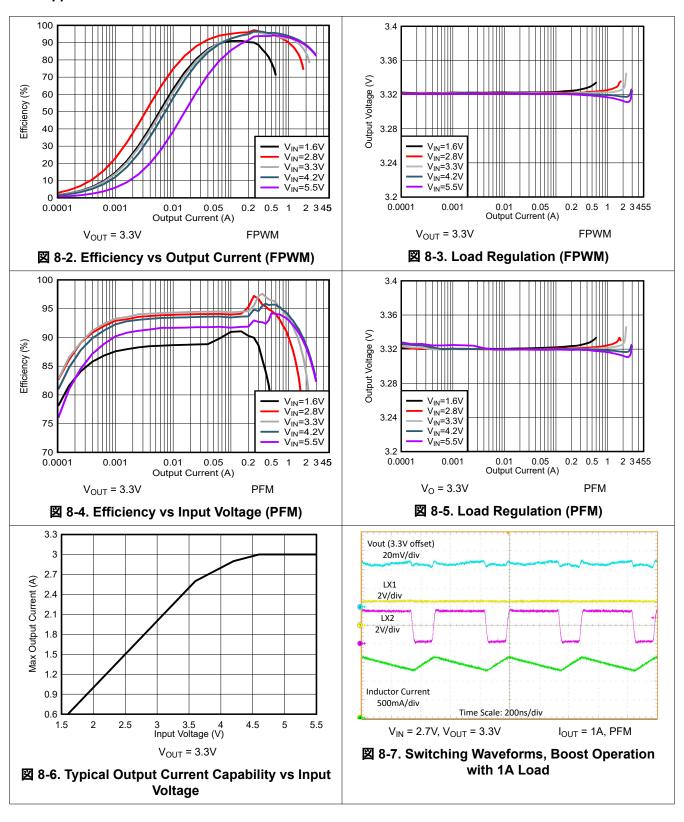
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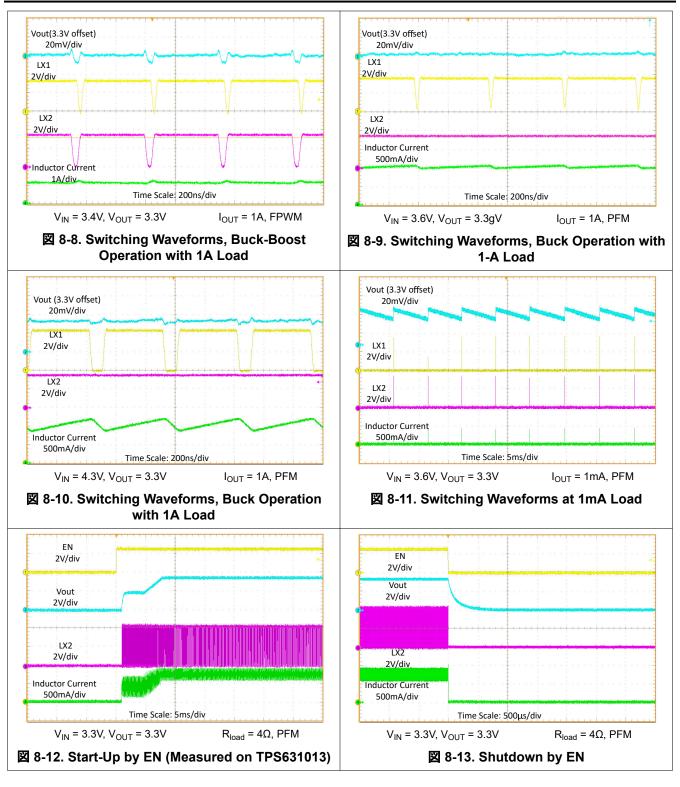
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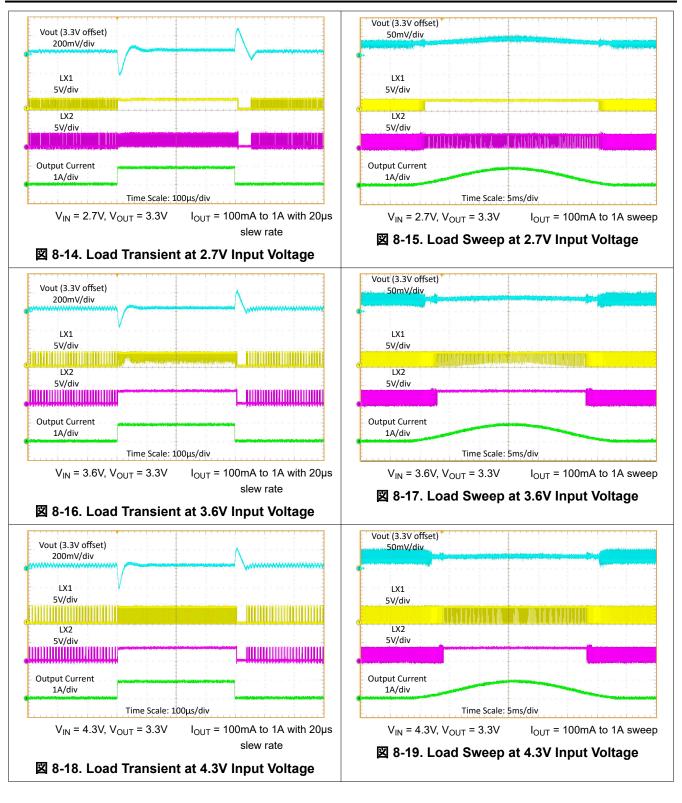
8.2.3 Application Curves











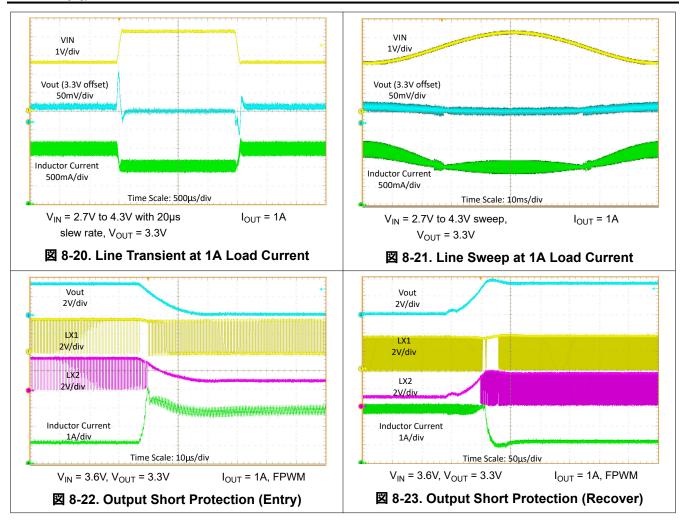


表 8-5. Components for Application Characteristic Curves for V_{OUT} = 3.3V

REFERENCE	DESCRIPTION (2)	PART NUMBER	MANUFACTURER ⁽¹⁾
U1	High Power Density 1.5A Buck-Boost Converter	TPS631012 or TPS631013	Texas Instruments
L1	1.0μH, 2.5mm x 2.0mm, 4.3A, 42mΩ	DFE252012P-1R0M=P2	MuRata
C1	22 μF, 0603, Ceramic Capacitor, ±20%, 6.3V	GRM187R61A226ME15	Murata
C2	47μF, 0805, Ceramic Capacitor, ±20%, 6.3V	GRM219R60J476ME44	Murata

⁽¹⁾ See the セクション 9.1.1.

8.3 Power Supply Recommendations

The TPS631012 and TPS631013 have no special requirements for its input power supply. The input power supply output current needs to be rated according to the supply voltage, output voltage, and output current.

8.4 Layout

8.4.1 Layout Guidelines

The PCB layout is an important step to maintain the high performance of the device.

- Place input and output capacitors as close as possible to the IC. Traces need to be kept short. Route wide
 and direct traces to the input and output capacitors results in low trace resistance and low parasitic
 inductance
- The sense trace connected to FB is signal trace. Keep these traces away from LX1 and LX2 nodes.

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⁽²⁾ For other output voltages, refer to for resistor values.



8.4.2 Layout Example

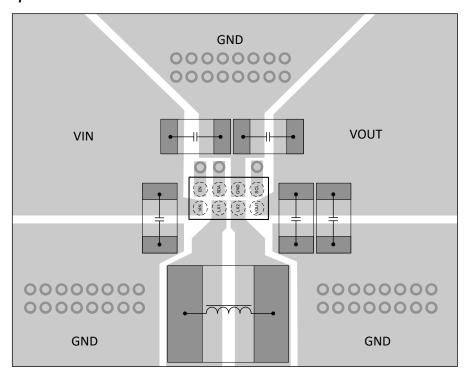


図 8-24. Layout Example



9 Device and Documentation Support

9.1 Device Support

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9.6 用語集

テキサス・インスツルメンツ用語集 この用語集には、用語や略語の一覧および定義が記載されています。

10 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (July 2023) to Revision A (January 2025)

Page



11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



11.1 Mechanical Data

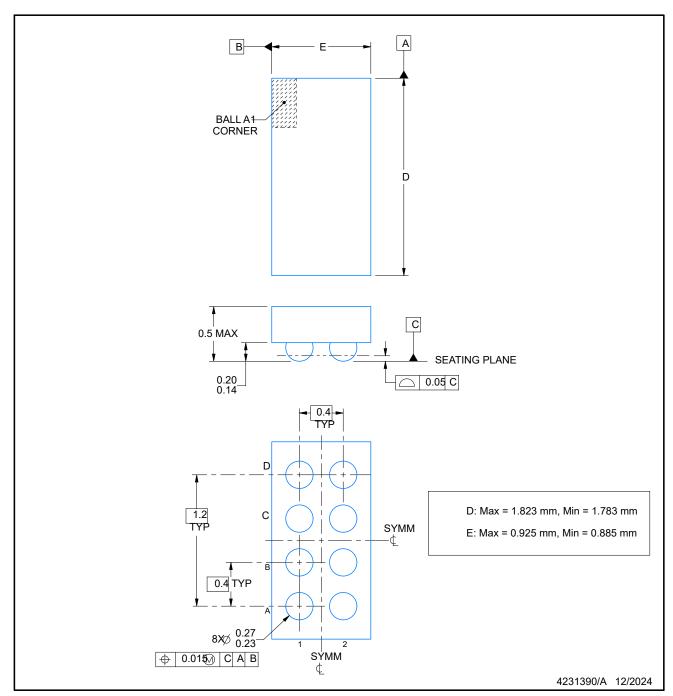
YBG0008-C02



PACKAGE OUTLINE

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

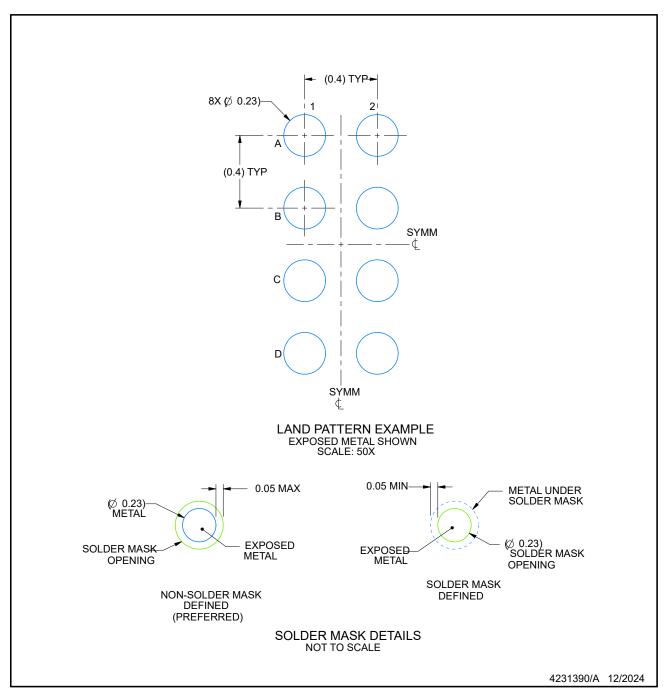
 2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

YBG0008-C02

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
 See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).

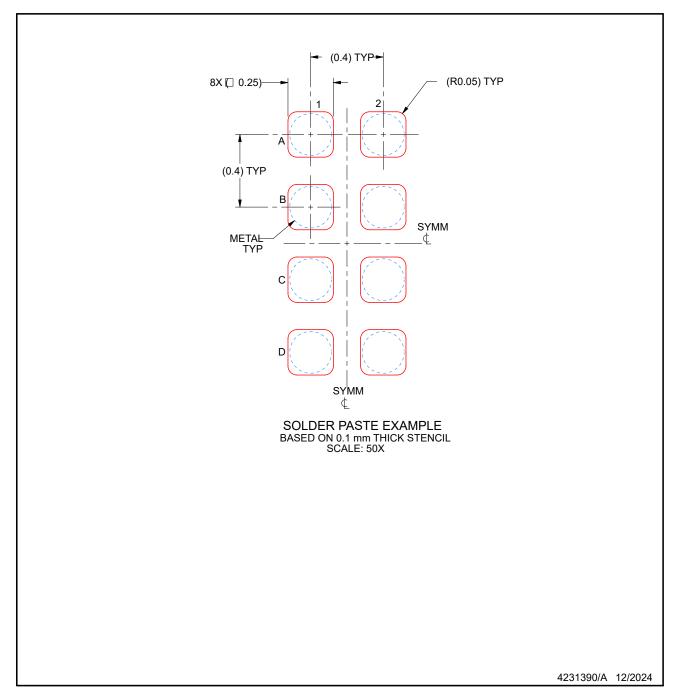


EXAMPLE STENCIL DESIGN

YBG0008-C02

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
TPS631012YBGR	ACTIVE	DSBGA	YBG	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	10L	Samples
TPS631013YBGR	ACTIVE	DSBGA	YBG	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	1P7	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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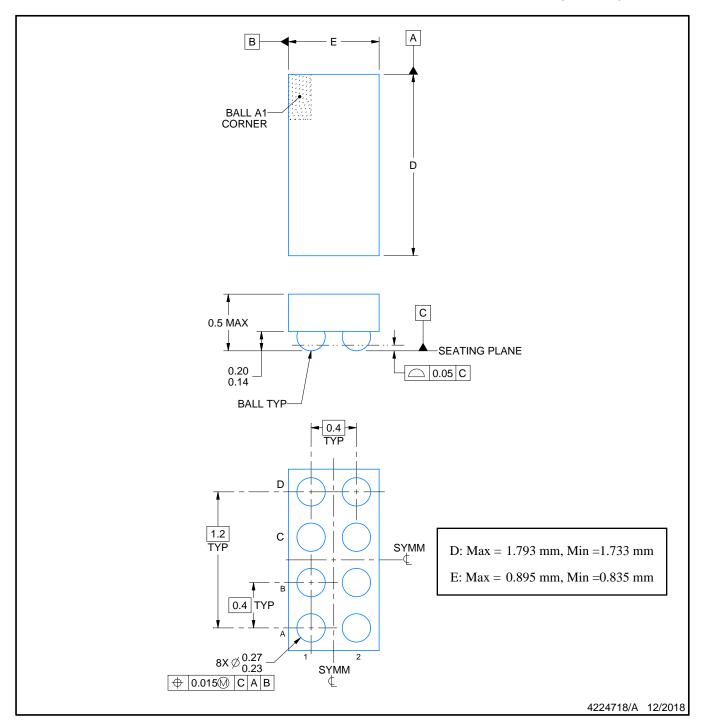


PACKAGE OPTION ADDENDUM

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DIE SIZE BALL GRID ARRAY



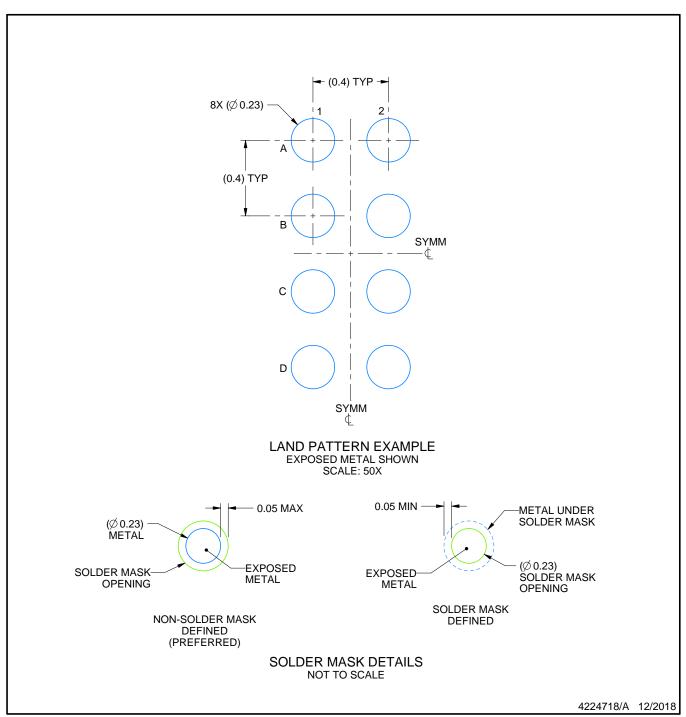
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

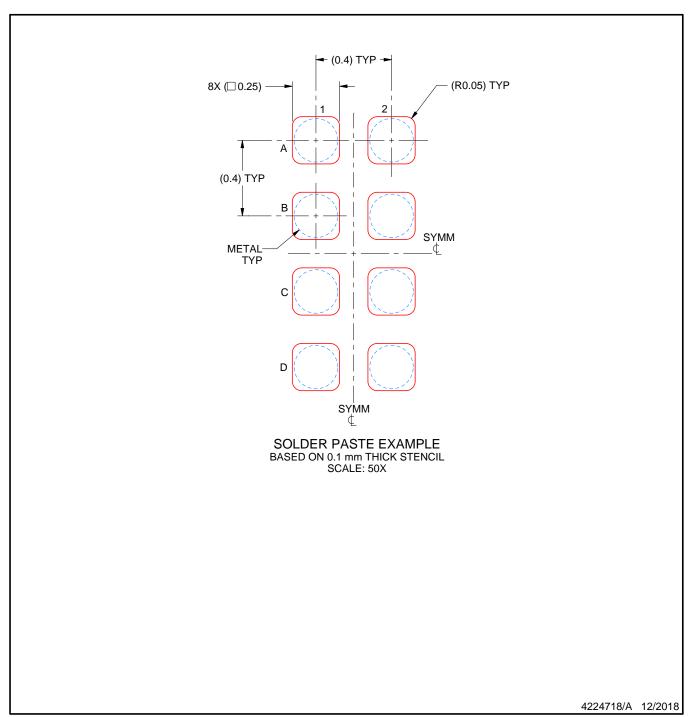


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. See Texas Instruments Literature No. SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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